

Abstract Submitted
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High Pressure Studies of the Metal-Insulator Transition in Pure NiS₂ ARNAB BANERJEE, YEJUN FENG, RAFAEL JARAMILLO, THOMAS F. ROSENBAUM, James Frank Institute, The University of Chicago, APS, ANL, SECTOR 4 AND 6 TEAM, JOE PLUTH/ANL APS SECTOR 13 COLLABORATION — Ni(S,Se)₂ is a one of the few Mott-Hubbard systems where a structural phase transition does not preclude quantitative study of the localization of charge at the $T = 0$ metal-insulator transition. Using diamond anvil cell techniques, we study the corresponding behavior of pure NiS₂ at its quantum critical point. We characterize the electronic, magnetic and structural behavior of this model system through a combination of transport and synchrotron scattering techniques, with a particular interest in the effects of disorder at a quantum phase transition.

Arnab Banerjee
The University of Chicago

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